FAIRCHILD SEMICONDUCTOR®

SuperFET™

FCP7N60 / FCPF7N60

600V N-Channel MOSFET

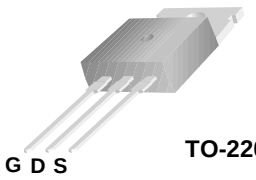
Features

- 650V @T_J = 150°C
- Typ. $R_{DS(on)}$ = 0.53Ω
- Ultra low gate charge (typ. Q_g = 25nC)
- Low effective output capacitance (typ. C_{oss}.eff = 60pF)
- 100% avalanche tested

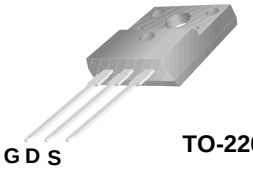
Description

SuperFET™ is, Farichild's proprietary, new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

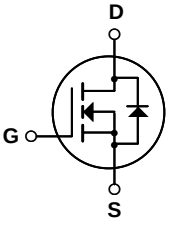
This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.



TO-220



TO-220F



Absolute Maximum Ratings

Symbol	Parameter		FCP7N60	FCPF7N60	Unit
V_{DSS}	Drain-Source Voltage		600		V
I_D	Drain Current	- Continuous (T_C = 25°C) - Continuous (T_C = 100°C)	7 4.4	7* 4.4*	A A
I_{DM}	Drain Current	- Pulsed (Note 1)	21	21*	A
V_{GSS}	Gate-Source voltage		± 30		V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	230		mJ
I_{AR}	Avalanche Current	(Note 1)	7		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	8.3		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
P_D	Power Dissipation	(T_C = 25°C) - Derate above 25°C	83 0.67	31 0.25	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300		°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FCP7N60	FCPF7N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.5	4.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

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Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCP7N60	FCP7N60	TO-220	-	-	50
FCPF7N60	FCPF7N60	TO-220F	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA, T_J = 25°C	600	--	--	V
		V_{GS} = 0V, I_D = 250μA, T_J = 150°C	--	650	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	--	0.6	--	V/°C
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	V_{GS} = 0V, I_D = 7A	--	700	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 600V, V_{GS} = 0V V_{DS} = 480V, T_C = 125°C	-- --	-- --	1 10	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 3.5A	--	0.53	0.6	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40V, I_D = 3.5A (Note 4)	--	6	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	--	710	920	pF
C_{oss}	Output Capacitance		--	380	500	pF
C_{rss}	Reverse Transfer Capacitance		--	34	--	pF
C_{oss}	Output Capacitance	V_{DS} = 480V, V_{GS} = 0V, f = 1.0MHz	--	22	29	pF
C_{oss} eff.	Effective Output Capacitance	V_{DS} = 0V to 400V, V_{GS} = 0V	--	60	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 300V, I_D = 7A, R_G = 25Ω	--	35	80	ns
t_r	Turn-On Rise Time		--	55	120	ns
$t_{d(off)}$	Turn-Off Delay Time		--	75	160	ns
t_f	Turn-Off Fall Time	(Note 4, 5)	--	32	75	ns
Q_g	Total Gate Charge	V_{DS} = 480V, I_D = 7A, V_{GS} = 10V	--	23	30	nC
Q_{gs}	Gate-Source Charge		--	4.2	5.5	nC
Q_{gd}	Gate-Drain Charge	(Note 4, 5)	--	11.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	7	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	21	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 7A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_S = 7A, dI_F/dt =100A/μs (Note 4)	--	360	--	ns
Q_{rr}	Reverse Recovery Charge		--	4.5	--	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS} = 7A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 7A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

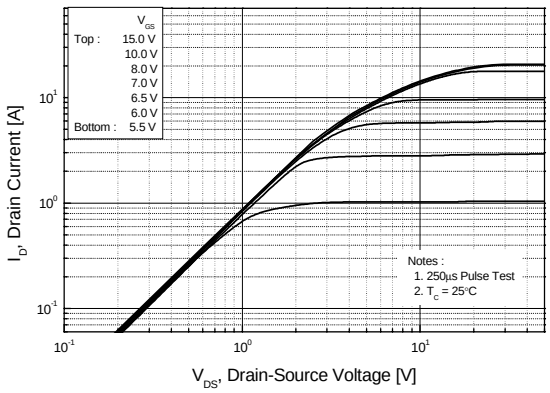


Figure 2. Transfer Characteristics

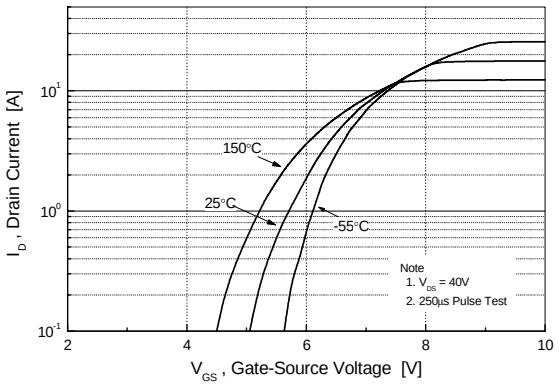


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

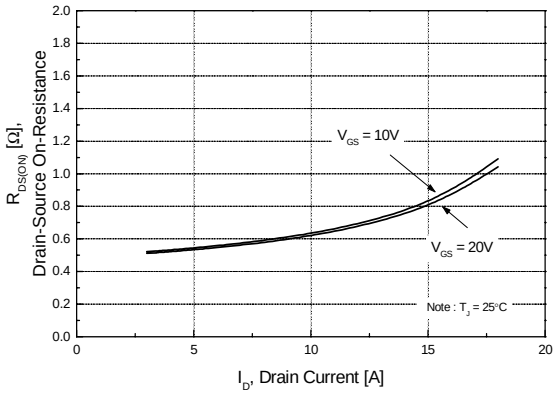


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

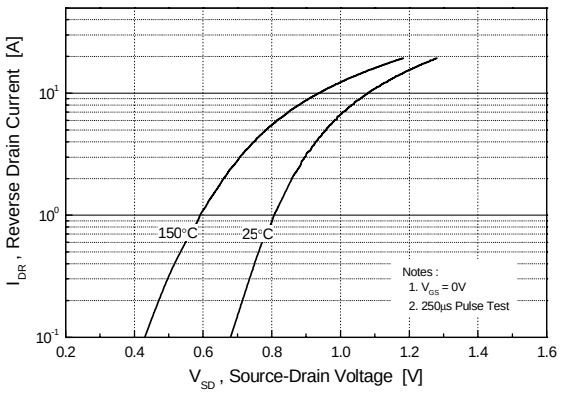


Figure 5. Capacitance Characteristics

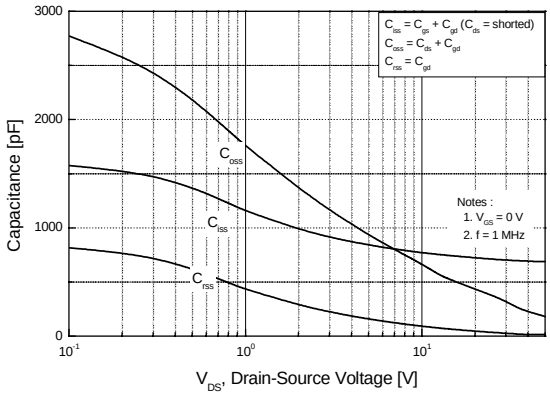
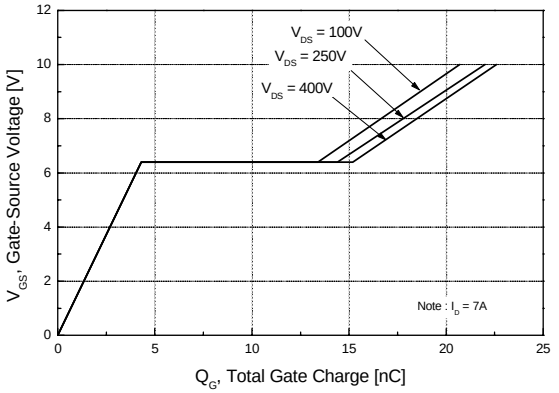


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

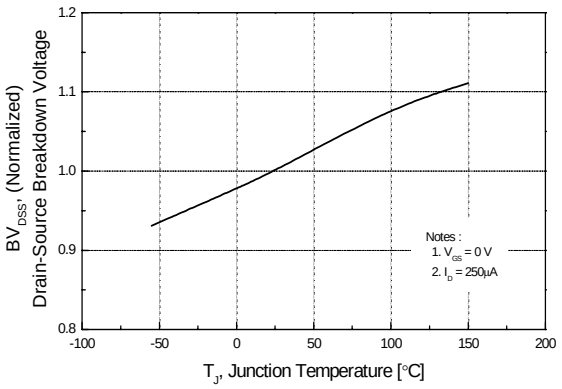


Figure 8. On-Resistance Variation vs. Temperature

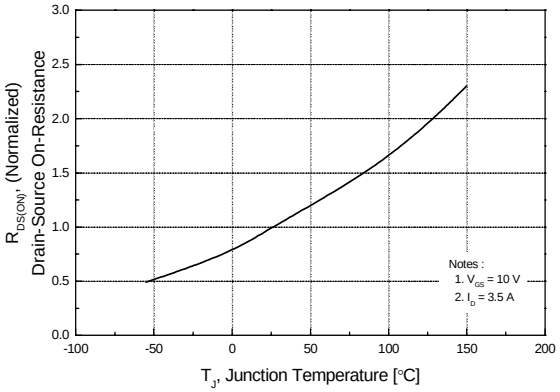


Figure 9-1. Maximum Safe Operating Area for FCP7N60

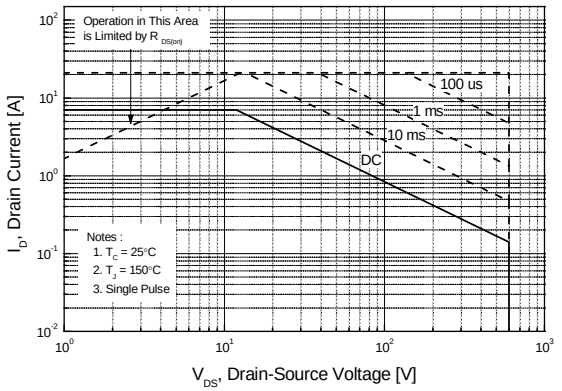


Figure 9-2. Maximum Safe Operating Area for FCPF7N60

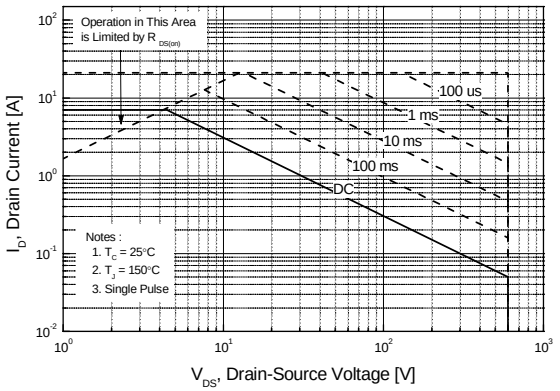
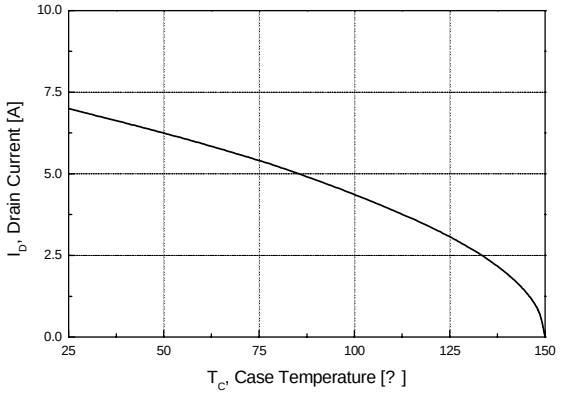


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve for FCP7N60

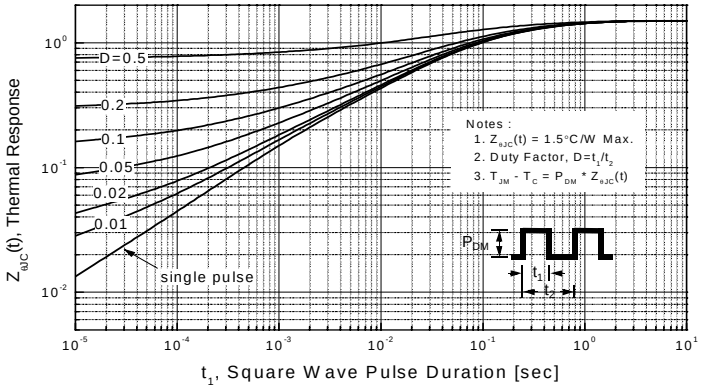
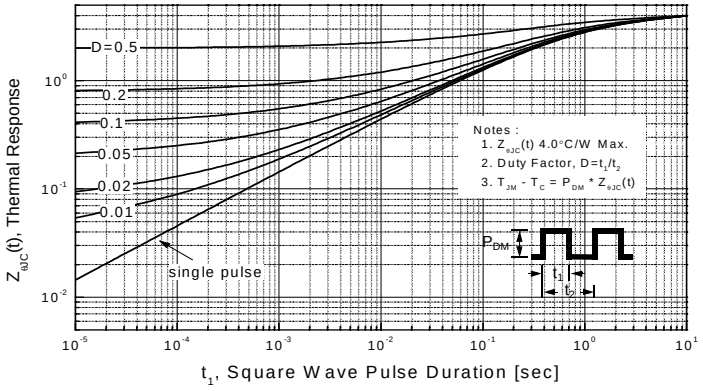
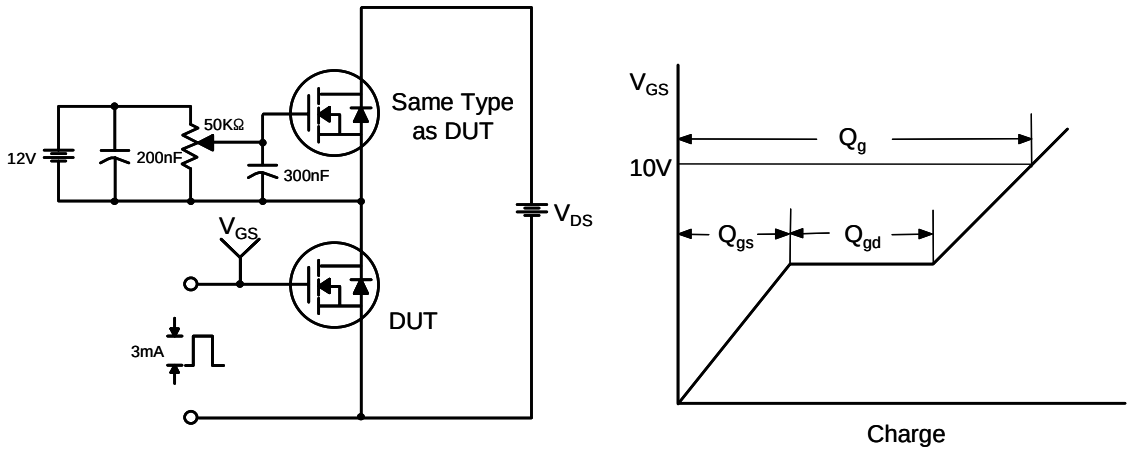


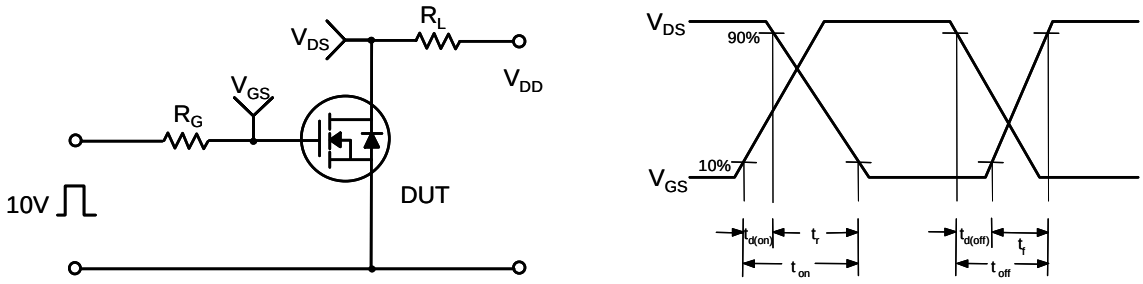
Figure 11-2. Transient Thermal Response Curve for FCPF7N60



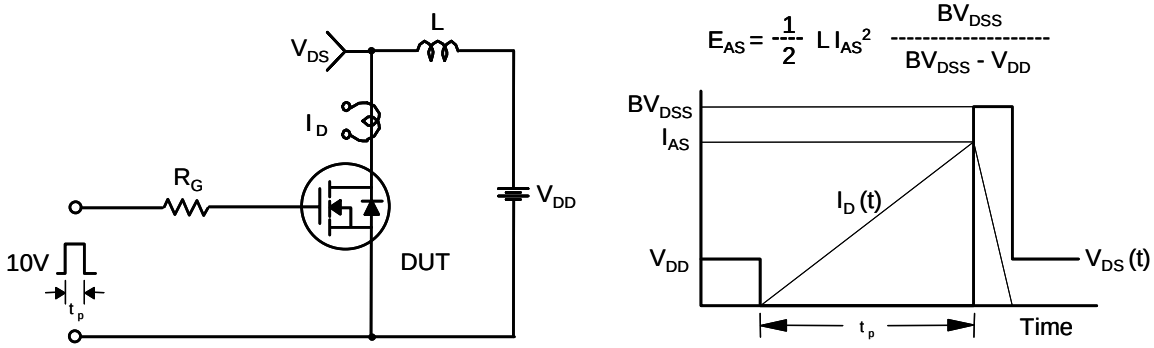
Gate Charge Test Circuit & Waveform



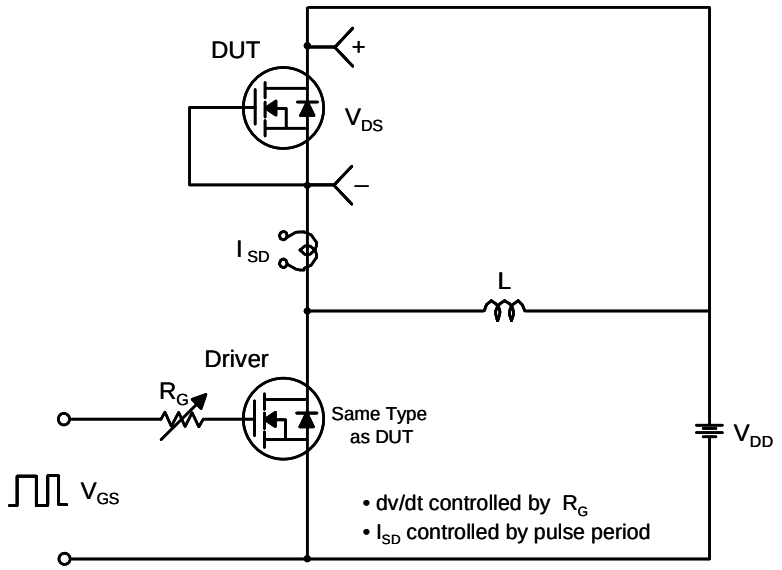
Resistive Switching Test Circuit & Waveforms

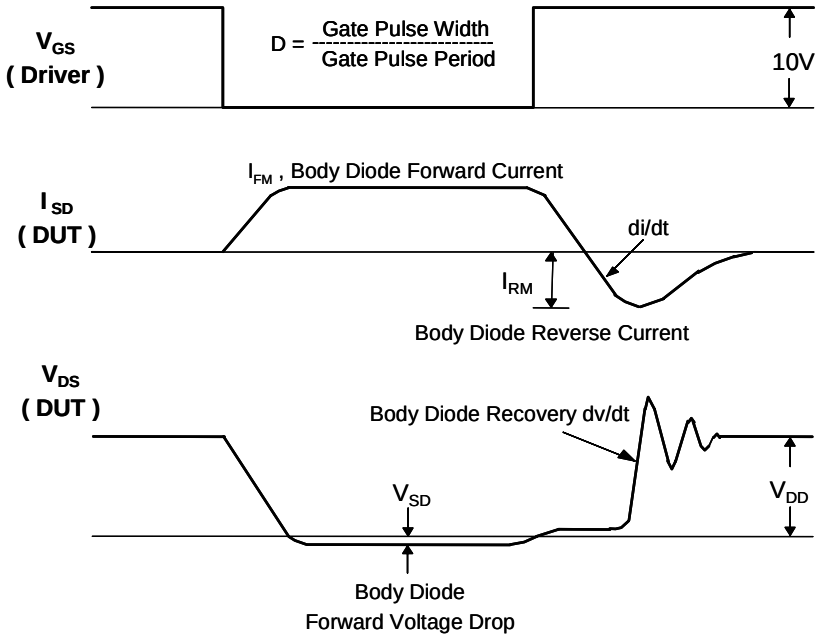


Unclamped Inductive Switching Test Circuit & Waveforms



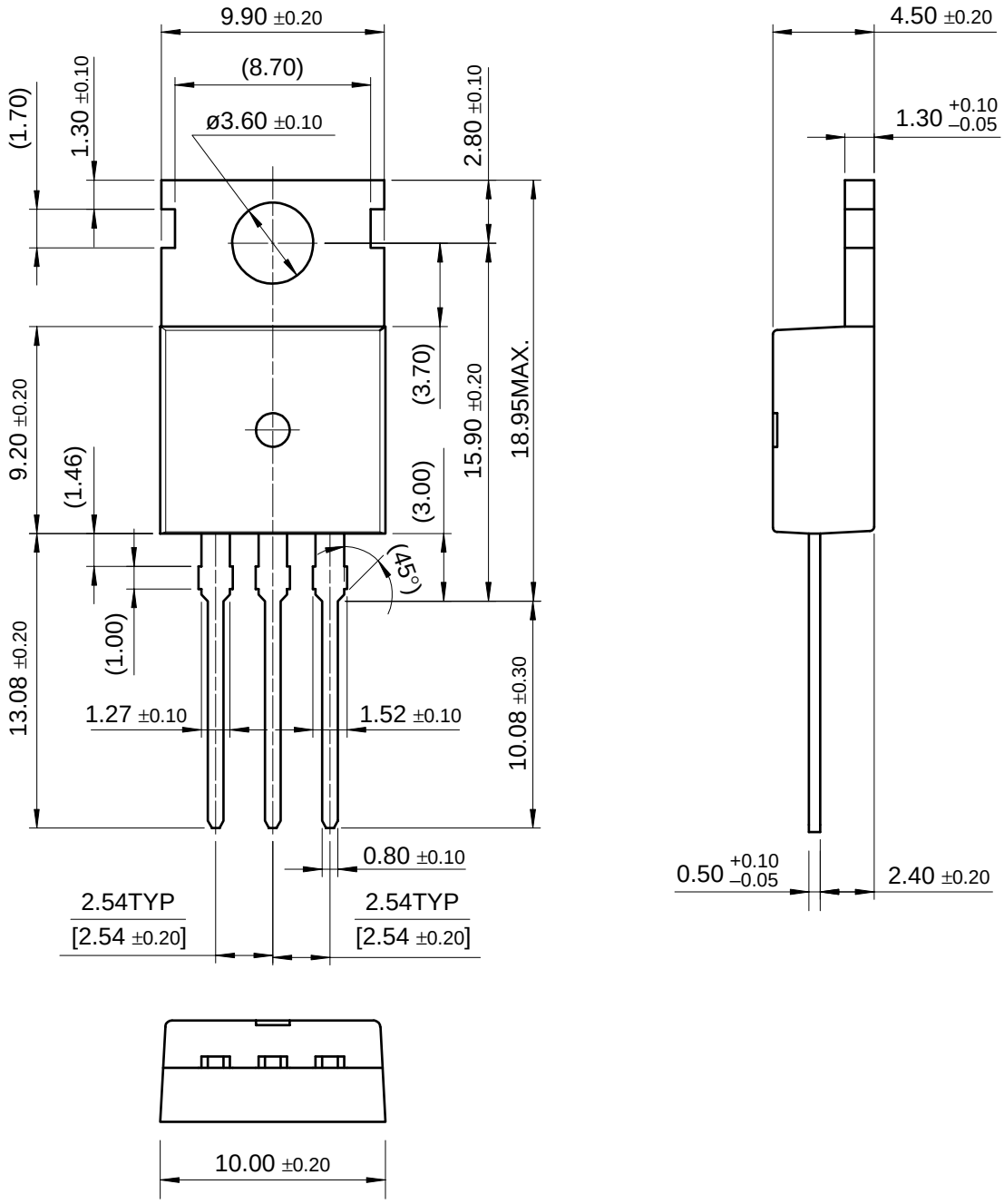
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

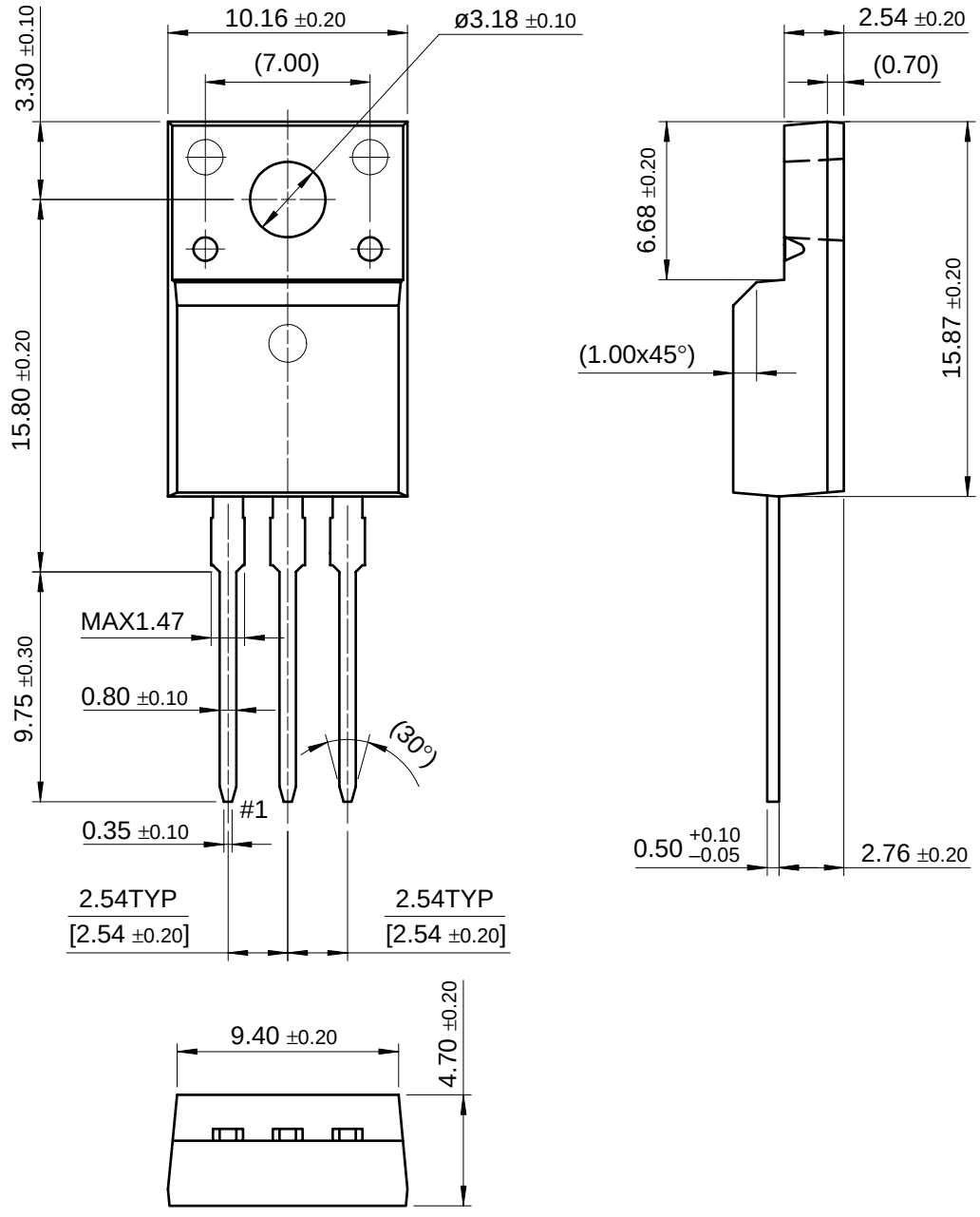
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Dimensions in Millimeters

Mechanical Dimensions (Continued)

TO-220F



Dimensions in Millimeters

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